

Po-Tsun Liu

List of Publications by Year in descending order

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295
papers

4,740
citations

101384

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298
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times ranked

3162
citing authors

#	ARTICLE	IF	CITATIONS
1	Vertical channel metal-oxide clusters as sensitive NO ₂ sensor with modulated response at room temperature. <i>Sensors and Actuators B: Chemical</i> , 2022, 354, 131222.	4.0	5
2	Performance Improvement for Ge FinFET CMOS Inverter With Supercritical Fluid Treatment. <i>IEEE Electron Device Letters</i> , 2022, 43, 838-841.	2.2	5
3	Radiation hardness of InWZnO thin film as resistive switching layer. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3
4	Investigation of deposition technique and thickness effect of HfO ₂ film in bilayer InWZnO-based conductive bridge random access memory. <i>Vacuum</i> , 2022, 201, 111123.	1.6	2
5	Extraction Method for Equivalent Oxide Thickness of a Thin High- κ Gate Insulator and Estimation of Field-Effect Mobility in Amorphous Oxide Semiconductor Nano-Sheet Junctionless Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 4791-4795.	1.6	3
6	15 μ s: Hydrogenated Amorphous Silicon Gate Driver on Array with Time-Division Driving Method for In μ Cell Touch Liquid-Crystal Display. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 184-187.	0.1	0
7	Enhanced Electrical Characteristics of Ge nMOSFET by Supercritical Fluid CO ₂ Treatment With H ₂ O ₂ Cosolvent. <i>IEEE Electron Device Letters</i> , 2021, 42, 645-648.	2.2	10
8	Oxygen Concentration Effect on Conductive Bridge Random Access Memory of InWZnO Thin Film. <i>Nanomaterials</i> , 2021, 11, 2204.	1.9	3
9	Impact of annealing environment on performance of InWZnO conductive bridge random access memory. <i>Vacuum</i> , 2021, 191, 110321.	1.6	6
10	Impact of O ₂ plasma treatment on novel amorphous oxide InWZnO on conductive bridge random access memory. <i>Surface and Coatings Technology</i> , 2021, 422, 127539.	2.2	4
11	Enhanced reliability and uniformity for Ge pMOSFET with low temperature supercritical fluid treatment. <i>Surface and Coatings Technology</i> , 2021, 423, 127632.	2.2	1
12	Effect of tungsten doping on the variability of InZnO conductive-bridging random access memory. <i>Nanotechnology</i> , 2021, 32, 035203.	1.3	4
13	Adjusting oxygen vacancy and resistance switching of InWZnO thin films by high-pressure oxidation technique. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	2
14	Numerical Analysis of Oxygen-Related Defects in Amorphous In-W-O Nanosheet Thin-Film Transistor. <i>Nanomaterials</i> , 2021, 11, 3070.	1.9	6
15	Strategy of Mitigating Breakdown Interference and Yield Loss in Crossbar Memory. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 6082-6086.	1.6	0
16	Improvement on thermal stability for indium gallium zinc oxide by oxygen vacancy passivation with supercritical fluid cosolvent oxidation. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	5
17	Annealing effects on resistive switching of IGZO-based CBRAM devices. <i>Vacuum</i> , 2020, 180, 109630.	1.6	12
18	High-reliability gate driver on array using noise sharing of precharging node for thin film transistor-liquid crystal display application. <i>Journal of the Society for Information Display</i> , 2020, 28, 965-978.	0.8	1

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19	Asymmetric Low Metal Contamination Ni-Induced Lateral Crystallization Polycrystalline-Silicon Thin-Film Transistors With Low OFF-State Currents for Back-End of Line (BEOL) Compatible Devices Applications. IEEE Journal of the Electron Devices Society, 2020, 8, 1317-1322.	1.2	1
20	Role of tungsten dopants in indium oxide thin-film transistor on radiation hardness technology. Applied Physics Letters, 2020, 116, .	1.5	26
21	Effect of Annealing Treatment on Performance of Ga ₂ O ₃ Conductive-Bridging Random-Access Memory. Journal of Electronic Materials, 2020, 49, 6817-6822.	1.0	12
22	High Performance Transparent a-IGZO Thin Film Transistors With ALD-HfO ₂ Gate Insulator on Colorless Polyimide Substrate. IEEE Nanotechnology Magazine, 2020, 19, 481-485.	1.1	18
23	Strong Read and Write Interference Induced by Breakdown Failure in Crossbar Arrays. IEEE Transactions on Electron Devices, 2020, 67, 5497-5504.	1.6	4
24	Highly durable and flexible gallium-based oxide conductive-bridging random access memory. Scientific Reports, 2019, 9, 14141.	1.6	35
25	Investigation of resistive switching in copper/InGaZnO/Al ₂ O ₃ -based memristor. Applied Physics Letters, 2019, 115, .	1.5	29
26	Photoresponsivity Enhancement and Extension of the Detection Spectrum for Amorphous Oxide Semiconductor Based Sensors. Advanced Electronic Materials, 2019, 5, 1800824.	2.6	27
27	Performance Enhancement for Tungsten-Doped Indium Oxide Thin Film Transistor by Hydrogen Peroxide as Cosolvent in Room-Temperature Supercritical Fluid Systems. ACS Applied Materials & Interfaces, 2019, 11, 22521-22530.	4.0	25
28	Bipolar resistive switching characteristics of tungsten-doped indium-zinc oxide conductive-bridging random access memory. Vacuum, 2019, 166, 226-230.	1.6	24
29	Two-Dimensional-Like Amorphous Indium Tungsten Oxide Nano-Sheet Junctionless Transistors with Low Operation Voltage. Scientific Reports, 2019, 9, 7579.	1.6	13
30	Multioutputs single-stage gate driver on array with wide temperature operable thin-film transistor liquid-crystal display for high resolution application. Journal of the Society for Information Display, 2019, 27, 21-33.	0.8	3
31	Mobility enhancement for high stability tungsten-doped indium-zinc oxide thin film transistors with a channel passivation layer. RSC Advances, 2018, 8, 6925-6930.	1.7	26
32	Investigation of low operation voltage InZnSnO thin-film transistors with different high-k gate dielectric by physical vapor deposition. Thin Solid Films, 2018, 660, 885-890.	0.8	22
33	Solving the integration problem of one transistor one memristor architecture with a Bi-layer IGZO film through synchronous process. Applied Physics Letters, 2018, 112, .	1.5	29
34	Enhanced stability of thin film transistors with double-stacked amorphous IWO/IWO:N channel layer. Semiconductor Science and Technology, 2018, 33, 065001.	1.0	9
35	Effects of Backchannel Passivation on Electrical Behavior of Hetero-Stacked a-IWO/IGZO Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2018, 7, Q17-Q20.	0.9	1
36	The Influence of Annealing Temperature on Amorphous Indium-Zinc-Tungsten Oxide Thin-Film Transistors. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700785.	0.8	10

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37	Electrical performance and stability of tungsten indium zinc oxide thin-film transistors. Materials Letters, 2018, 214, 293-296.	1.3	13
38	Interchangeable Hebbian and Anti-Hebbian STDP Applied to Supervised Learning in Spiking Neural Network. , 2018, , .		5
39	(Invited) High Performance Amorphous In-W-Zn-O Thin Film Transistor with Ultra-Thin Active Channel for Low Voltage Operation. ECS Transactions, 2018, 86, 91-93.	0.3	3
40	Low Thermal Budget Amorphous Indium Tungsten Oxide Nano-Sheet Junctionless Transistors with Near Ideal Subthreshold Swing. , 2018, , .		4
41	The influence on electrical characteristics of amorphous indium tungsten oxide thin film transistors with multi-stacked active layer structure. Thin Solid Films, 2018, 666, 94-99.	0.8	12
42	Back-Channel Etched Double Layer In-W-O/In-W-Zn-O Thin-Film Transistors. ECS Transactions, 2018, 86, 111-114.	0.3	2
43	TAOS based Cu/TiW/IGZO/Ga ₂ O ₃ /Pt bilayer CBRAM for low-power display technology. Surface and Coatings Technology, 2018, 354, 169-174.	2.2	26
44	Performance improvements of tungsten and zinc doped indium oxide thin film transistor by fluorine based double plasma treatment with a high-K gate dielectric. Thin Solid Films, 2018, 665, 117-122.	0.8	12
45	Highly Responsive Blue Light Sensor with Amorphous Indium-Zinc-Oxide Thin-Film Transistor based Architecture. Scientific Reports, 2018, 8, 8153.	1.6	47
46	Effect of interfacial layer on device performance of metal oxide thin-film transistor with a multilayer high-k gate stack. Thin Solid Films, 2018, 660, 578-584.	0.8	18
47	High mobility tungsten-doped thin-film transistor on polyimide substrate with low temperature process. , 2018, , .		2
48	28-4: Design of High Reliability a-Si:H TFT Gate Driver with Threshold Voltage Compensation on TFT-LCD Application. Digest of Technical Papers SID International Symposium, 2018, 49, 365-368.	0.1	2
49	Impact of post deposition annealing on resistive switching in GaIn-OIn-based conductive-bridge RAM devices. , 2018, , .		0
50	TFT Materials and Devices. , 2018, , 12-16.		2
51	Annealing Effect on Amorphous Indium-Zinc-Tungsten-Oxide Thin-Film Transistors. , 2018, , .		1
52	19â€1: <i>Invited Paper:</i> Stability of Sputtered Amorphous Tungstenâ€doped Indium Oxide Based Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 225-227.	0.1	1
53	Stability study of indium tungsten oxide thin-film transistors annealed under various ambient conditions. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600465.	0.8	14
54	Thickness-dependent magnetotransport properties and terahertz response of topological insulator Bi ₂ Te ₃ thin films. Journal of Alloys and Compounds, 2017, 692, 972-979.	2.8	25

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55	Design of dual outputs single stage a-Si:H TFT gate driver for high resolution TFT-LCD application. Journal of the Society for Information Display, 2016, 24, 330-337.	0.8	3
56	Silicon induced stability and mobility of indium zinc oxide based bilayer thin film transistors. Applied Physics Letters, 2016, 109, .	1.5	10
57	Modification of intrinsic defects in IZO/IGZO thin films for reliable bilayer thin film transistors. RSC Advances, 2016, 6, 75693-75698.	1.7	18
58	Design of Bi-Directional Transmission Gate Driver in Amorphous Silicon Technology for TFT-LCD Application. ECS Transactions, 2016, 75, 55-60.	0.3	0
59	Influence of Passivation Layers on Characteristics of High Mobility Amorphous Indium-Zinc-Tin-Oxide Thin-Film Transistors. ECS Transactions, 2016, 75, 163-168.	0.3	5
60	Reduced parasitic contact resistance and highly stable operation in a-In-Ga-Zn-O thin-film transistors with microwave treatment. Thin Solid Films, 2016, 619, 148-152.	0.8	5
61	Enhancement of reliability and stability for transparent amorphous indium-zinc-tin-oxide thin film transistors. RSC Advances, 2016, 6, 106374-106379.	1.7	40
62	Effects of Nitrogen on Amorphous Nitrogenated InGaZnO (a-IGZO:N) Thin Film Transistors. Journal of Display Technology, 2016, 12, 1070-1077.	1.3	21
63	Suppression of photo-bias induced instability for amorphous indium tungsten oxide thin film transistors with bi-layer structure. Applied Physics Letters, 2016, 108, 261603.	1.5	28
64	Photoluminescence and Reliability Study of ZnO Cosputtered IGZO Thin-Film Transistors Under Various Ambient Conditions. IEEE Transactions on Electron Devices, 2016, 63, 1578-1581.	1.6	15
65	Performance and reliability of non-linear Al-Zn-Sn-O based resistive random access memory. , 2015, , .		2
66	P26: High Capacity Memory using Oxide Based Schottky Diode and Unipolar Resistive Array. Digest of Technical Papers SID International Symposium, 2015, 46, 1213-1216.	0.1	0
67	P18: Extraction and Simulation with Time Dependent V_{th} Shift Model for IGZO Panel. Digest of Technical Papers SID International Symposium, 2015, 46, 1184-1187.	0.1	1
68	Electrical characteristics of InGaZnO thin film transistor prepared by co-sputtering dual InGaZnO and ZnO targets. RSC Advances, 2015, 5, 51983-51989.	1.7	22
69	Study on transparent amorphous indium oxide thin film transistors technology. , 2015, , .		0
70	High Endurance and Multilevel Operation in Oxide Semiconductor-Based Resistive RAM Using Thin-Film Transistor as a Selector. ECS Solid State Letters, 2015, 4, Q41-Q43.	1.4	13
71	Structural, optical, and photoluminescence study of ZnO/IGZO thin film for thin film transistor application. Materials Letters, 2015, 151, 53-56.	1.3	25
72	P20: Performance Improvement for High Mobility Amorphous Indium-Zinc-Tin-Oxide Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2014, 45, 1017-1020.	0.1	3

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73	Effect of Annealing on Defect Elimination for High Mobility Amorphous Indium-Zinc-Tin-Oxide Thin-Film Transistor. IEEE Electron Device Letters, 2014, 35, 1103-1105.	2.2	79
74	Improvement of Resistive Switching Uniformity for Al ³⁺ Zn ²⁺ Sn ⁴⁺ O-Based Memory Device With Inserting HfO ₂ Layer. IEEE Electron Device Letters, 2014, 35, 1233-1235.	2.2	21
75	InZnSnO-Based Electronic Devices for Flat Panel Display Applications. ECS Journal of Solid State Science and Technology, 2014, 3, Q3054-Q3057.	0.9	2
76	Photovoltaic electrical properties of aqueous grown ZnO antireflective nanostructure on Cu(In,Ga)Se ₂ thin film solar cells. Optics Express, 2014, 22, A13.	1.7	11
77	Polystyrene-block-poly(methylmethacrylate) composite material film as a gate dielectric for plastic thin-film transistor applications. RSC Advances, 2014, 4, 18493-18502.	1.7	11
78	Characteristic Evolution From Rectifier Schottky Diode to Resistive-Switching Memory With Al-Doped Zinc Tin Oxide Film. IEEE Transactions on Electron Devices, 2014, 61, 1071-1076.	1.6	22
79	Efficiency enhancement of non-selenized Cu(In,Ga)Se ₂ solar cells employing scalable low-cost antireflective coating. Nanoscale Research Letters, 2014, 9, 331.	3.1	8
80	A promising sputtering route for dense Cu ₂ ZnSnS ₄ absorber films and their photovoltaic performance. Solar Energy Materials and Solar Cells, 2014, 128, 275-282.	3.0	28
81	Investigation on amorphous InGaZnO based resistive switching memory with low-power, high-speed, high reliability. Thin Solid Films, 2013, 549, 54-58.	0.8	42
82	Investigation on plasma treatment for transparent Al ³⁺ Zn ²⁺ Sn ⁴⁺ O thin film transistor application. Thin Solid Films, 2013, 549, 36-41.	0.8	7
83	Effects of ZnO-nanostructure antireflection coatings on sulfurization-free Cu ₂ ZnSnS ₄ absorber deposited by single-step co-sputtering process. Applied Physics Letters, 2013, 103, .	1.5	19
84	Role of Oxygen in Amorphous In-Ga-Zn-O Thin Film Transistor for Ambient Stability. ECS Journal of Solid State Science and Technology, 2013, 2, Q1-Q5.	0.9	21
85	Controlled deposition of new organic ultrathin film as a gate dielectric layer for advanced flexible capacitor devices. Journal of Materials Science: Materials in Electronics, 2013, 24, 1807-1812.	1.1	4
86	Design of Bidirectional and Low Power Consumption Gate Driver in Amorphous Silicon Technology for TFT-LCD Application. Journal of Display Technology, 2013, 9, 91-99.	1.3	40
87	Polycrystalline Cu(In, Ga)Se ₂ Thin Films and PV Devices Sputtered From a Binary Target without Additional Selenization. ECS Transactions, 2013, 50, 53-58.	0.3	0
88	Influence of channel layer and passivation layer on the stability of amorphous InGaZnO thin film transistors. Microelectronics Reliability, 2013, 53, 1879-1885.	0.9	34
89	Effect of oxygen plasma on the surface states of ZnO films used to produce thin-film transistors on soft plastic sheets. Journal of Materials Chemistry C, 2013, 1, 6613.	2.7	65
90	(Invited) Transparent Amorphous Oxide Semiconductors for System on Panel Applications. ECS Transactions, 2013, 50, 257-268.	0.3	5

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91	Oxygen Plasma Functioning of Charge Carrier Density in Zinc Oxide Thin-Film Transistors. Applied Physics Express, 2013, 6, 076501.	1.1	20
92	Effects of Microwave Annealing on Nitrogenated Amorphous In-Ga-Zn-O Thin-Film Transistor for Low Thermal Budget Process Application. IEEE Electron Device Letters, 2013, 34, 1157-1159.	2.2	62
93	Multilevel resistive switching memory with amorphous InGaZnO-based thin film. Applied Physics Letters, 2013, 102, .	1.5	62
94	16.4: Photostability Improvement of InGaZnO TFTs by Introducing a Transparent UV Shielding Layer. Digest of Technical Papers SID International Symposium, 2013, 44, 178-181.	0.1	2
95	Electrical Performance Enhancement of Al-Zn-Sn-O Thin Film Transistor by Supercritical Fluid Treatment. IEEE Electron Device Letters, 2013, 34, 1154-1156.	2.2	11
96	P.12: Development of Post-annealing Method for Flexible Oxide TFTs Application. Digest of Technical Papers SID International Symposium, 2013, 44, 1026-1028.	0.1	0
97	A non-selenization technology by co-sputtering deposition for solar cell applications. Optics Letters, 2012, 37, 2760.	1.7	17
98	Bipolar resistive switching characteristics of Al-doped zinc tin oxide for nonvolatile memory applications. Applied Physics Letters, 2012, 101, 052901.	1.5	45
99	Effects of microwave annealing on electrical enhancement of amorphous oxide semiconductor thin film transistor. Applied Physics Letters, 2012, 101, .	1.5	82
100	Surface potential and electric field mapping of p-well/n-well junction by secondary electron potential contrast and in-situ nanoprobe biasing. , 2012, , .		0
101	P-8: Low Power Gate Driver Circuits for Narrow Bezel Panel Application. Digest of Technical Papers SID International Symposium, 2012, 43, 1076-1078.	0.1	8
102	P-76: Resistive Switching Memory Device Based on Amorphous Al-Zn-Sn-O Film for Flexible Electronics Application. Digest of Technical Papers SID International Symposium, 2012, 43, 1340-1342.	0.1	2
103	Surface potential mapping of p+/n-well junction by secondary electron potential contrast with in situ nano-probe biasing. Microelectronic Engineering, 2012, 95, 5-9.	1.1	3
104	Ambient Stability Enhancement of Thin-Film Transistor With InGaZnO Capped With InGaZnO:N Bilayer Stack Channel Layers. IEEE Electron Device Letters, 2011, 32, 1397-1399.	2.2	41
105	Profiling p^+/n -Well Junction by Nanoprobing and Secondary Electron Potential Contrast. IEEE Electron Device Letters, 2011, 32, 868-870.	2.2	4
106	Design of Analog Pixel Memory for Low Power Application in TFT-LCDs. Journal of Display Technology, 2011, 7, 62-69.	1.3	11
107	Design of Integrated Gate Driver With Threshold Voltage Drop Cancellation in Amorphous Silicon Technology for TFT-LCD Application. Journal of Display Technology, 2011, 7, 657-664.	1.3	35
108	Role of environmental and annealing conditions on the passivation-free In-Ga-Zn-O TFT. Thin Solid Films, 2011, 520, 1489-1494.	0.8	74

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109	Electrical and Photosensitive Characteristics of a-IGZO TFTs Related to Oxygen Vacancy. IEEE Transactions on Electron Devices, 2011, 58, 1121-1126.	1.6	217
110	Effect of high-pressure H ₂ O treatment on elimination of interfacial GeO _x layer between ZrO ₂ and Ge stack. Applied Physics Letters, 2011, 99, 082907.	1.5	8
111	Inspection of the Current-Mirror Mismatch by Secondary Electron Potential Contrast With In Situ Nanoprobe Biasing. IEEE Electron Device Letters, 2011, 32, 1418-1420.	2.2	3
112	Nitrogenated amorphous InGaZnO thin film transistor. Applied Physics Letters, 2011, 98, .	1.5	74
113	Impact of Negative-Bias-Temperature-Instability on Channel Bulk of Polysilicon TFT by Gated PIN Diode Analysis. Electrochemical and Solid-State Letters, 2011, 14, H194.	2.2	1
114	Thin Film Transistor with Al _{0.5} Ni _{0.5} La Alloy Gate Metallization Technology. Electrochemical and Solid-State Letters, 2011, 14, H57.	2.2	4
115	Stabilization of oxide-based thin-film transistors. SPIE Newsroom, 2011, , .	0.1	0
116	P-27: Novel AlNiLa Serves as Gate Electrodes of a-TFT for AMLCD. Digest of Technical Papers SID International Symposium, 2010, 41, 1322.	0.1	0
117	P40: Design of Analog Pixel Memory Circuit with Low Temperature Polycrystalline Silicon TFTs for Low Power Application. Digest of Technical Papers SID International Symposium, 2010, 41, 1363-1366.	0.1	7
118	P-64: Using Electroless Plating Technology for Copper Metallization in AMLCD Application. Digest of Technical Papers SID International Symposium, 2010, 41, 1479.	0.1	0
119	Mechanical bending effect on the photo leakage currents characteristic of amorphous silicon thin film transistors. Solid-State Electronics, 2010, 54, 1485-1487.	0.8	2
120	Using electroless plating Cu technology for TFT-LCD application. Surface and Coatings Technology, 2010, 205, 1497-1501.	2.2	14
121	Photosensor application of amorphous InZnO-based thin film transistor. Proceedings of SPIE, 2010, , .	0.8	0
122	High-gain complementary inverter with InGaZnO/pentacene hybrid ambipolar thin film transistors. Applied Physics Letters, 2010, 97, 083505.	1.5	26
123	Effects of postgate dielectric treatment on germanium-based metal-oxide-semiconductor device by supercritical fluid technology. Applied Physics Letters, 2010, 96, 112902.	1.5	6
124	Effect of bias stress on mechanically strained low temperature polycrystalline silicon thin film transistor on stainless steel substrate. Applied Physics Letters, 2009, 95, .	1.5	25
125	Environment-dependent metastability of passivation-free indium zinc oxide thin film transistor after gate bias stress. Applied Physics Letters, 2009, 95, .	1.5	201
126	Application of secondary electron potential contrast on junction leakage isolation. Applied Physics Letters, 2009, 95, 122105.	1.5	10

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127	Charge pumping method for photosensor application by using amorphous indium-zinc oxide thin film transistors. Applied Physics Letters, 2009, 94, 242101.	1.5	44
128	Application of Supercritical CO ₂ Fluid for Dielectric Improvement of SiO _x Film. Electrochemical and Solid-State Letters, 2009, 12, H35.	2.2	11
129	Compensation Pixel Circuit Using LTPS TFT For AMOLED Displays. ECS Transactions, 2009, 16, 387-392.	0.3	0
130	Improvement of Electron-Gun Evaporated Aluminum Oxide for Pentacene Thin-Film Transistor. Electrochemical and Solid-State Letters, 2009, 12, H11.	2.2	6
131	Organic Light-Emitting Diodes Tuned with an External Color Tuning Layer. ECS Transactions, 2009, 16, 11-15.	0.3	1
132	Effect of Passivation Layer on the Reliability of Flexible a-Si:H TFTs. ECS Transactions, 2009, 16, 339-343.	0.3	0
133	Innovative Voltage Driving Pixel Circuit Using Organic Thin-Film Transistor for AMOLEDs. Journal of Display Technology, 2009, 5, 224-227.	1.3	27
134	P-15: Retarded Photoreaction Reversibility of a-IZO TFT for Light Sensor Applications. Digest of Technical Papers SID International Symposium, 2009, 40, 1132.	0.1	2
135	Performance enhancement of excimer laser crystallized poly-Si thin film transistors with fluorine implantation technology. Thin Solid Films, 2008, 516, 3128-3132.	0.8	0
136	Application of fluorine doped oxide (SiOF) spacers for improving reliability in low temperature polycrystalline thin film transistors. Thin Solid Films, 2008, 517, 1204-1208.	0.8	0
137	Anomalous Gate-Edge Leakage Induced by High Tensile Stress in NMOSFET. IEEE Electron Device Letters, 2008, 29, 1249-1251.	2.2	3
138	Reduction of photoleakage current in polycrystalline silicon thin-film transistor using NH ₃ plasma treatment on buffer layer. Applied Physics Letters, 2008, 92, 153507.	1.5	3
139	Passivation Effect of Poly-Si Thin-Film Transistors With Fluorine-Ion-Implanted Spacers. IEEE Electron Device Letters, 2008, 29, 603-605.	2.2	4
140	Elimination of Photoleakage Current in Poly-Si TFTs Using a Metal-Shielding Structure. Electrochemical and Solid-State Letters, 2008, 11, J34.	2.2	3
141	Dielectric Hafnium Oxide Improved by Supercritical Carbon Dioxide Fluid Treatment for Pentacene Thin-Film Transistors. Electrochemical and Solid-State Letters, 2008, 11, H165.	2.2	12
142	Variable Temperature Measurement on Operating Pentacene-Based OTFT. Materials Research Society Symposia Proceedings, 2008, 1091, 1.	0.1	2
143	Modeling of nitrogen profile effects on direct tunneling probability in ultrathin nitrided oxides. Applied Physics Letters, 2008, 92, 022112.	1.5	1
144	Formation of cobalt-silicide nanocrystals in Ge-doped dielectric layer for the application on nonvolatile memory. Applied Physics Letters, 2008, 92, 152115.	1.5	8

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145	A low temperature fabrication of HfO ₂ films with supercritical CO ₂ fluid treatment. Journal of Applied Physics, 2008, 103, .	1.1	24
146	Low temperature improvement on silicon oxide grown by electron-gun evaporation for resistance memory applications. Applied Physics Letters, 2008, 93, 052903.	1.5	9
147	The Strain Effects on Flexible a-Si:H TFTs. ECS Transactions, 2008, 16, 333-337.	0.3	0
148	Reliability study on tri-gate nanowires poly-Si TFTs under DC and AC hot-carrier stress. , 2007, , .		1
149	High-Performance Polycrystalline-Silicon TFT by Heat-Retaining Enhanced Lateral Crystallization. IEEE Electron Device Letters, 2007, 28, 722-724.	2.2	3
150	Analysis of Parasitic Resistance and Channel Sheet Conductance of a-Si:H TFT under Mechanical Bending. Electrochemical and Solid-State Letters, 2007, 10, J49.	2.2	5
151	Nonvolatile Si ⁺ •SiO ₂ ⁺ •SiN ⁺ •SiO ₂ ⁺ •Si type polycrystalline silicon thin-film-transistor memory with nanowire channels for improvement of erasing characteristics. Applied Physics Letters, 2007, 91, 193103.	1.5	11
152	Suppression of Schottky leakage current in island-in amorphous silicon thin film transistors with the Cu ⁺ •CuMg as source/drain metal. Applied Physics Letters, 2007, 91, 062103.	1.5	9
153	Effects of Supercritical Fluids Activation on Carbon Nanotube Field Emitters. IEEE Nanotechnology Magazine, 2007, 6, 29-34.	1.1	16
154	Using double layer CoSi ₂ nanocrystals to improve the memory effects of nonvolatile memory devices. Applied Physics Letters, 2007, 90, 212108.	1.5	35
155	Memory characteristics of Co nanocrystal memory device with HfO ₂ as blocking oxide. Applied Physics Letters, 2007, 90, 132102.	1.5	57
156	Low-temperature method for enhancing sputter-deposited HfO ₂ films with complete oxidization. Applied Physics Letters, 2007, 91, 012109.	1.5	36
157	Nonvolatile memory characteristics of nickel-silicon-nitride nanocrystal. Applied Physics Letters, 2007, 91, 082103.	1.5	19
158	Formation of stacked Ni silicide nanocrystals for nonvolatile memory application. Applied Physics Letters, 2007, 90, 112108.	1.5	45
159	Photo-leakage-current characteristic of F incorporated hydrogenated amorphous silicon thin film transistor. Applied Physics Letters, 2007, 90, 192114.	1.5	4
160	n ⁺ -doped-layer-free microcrystalline silicon thin film transistors fabricated with the CuMg as source/drain metal. Applied Physics Letters, 2007, 91, 022113.	1.5	4
161	Nonvolatile polycrystalline silicon thin-film-transistor memory with oxide/nitride/oxide stack gate dielectrics and nanowire channels. Applied Physics Letters, 2007, 90, 122111.	1.5	30
162	Nonvolatile low-temperature polycrystalline silicon thin-film-transistor memory devices with oxide-nitride-oxide stacks. Applied Physics Letters, 2007, 90, 182115.	1.5	15

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164	The Instability of a-Si:H TFT under Mechanical Strain with High Frequency ac Bias Stress. Electrochemical and Solid-State Letters, 2007, 10, J113.	2.2	10
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